



Description

The NTMD5838NL uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.



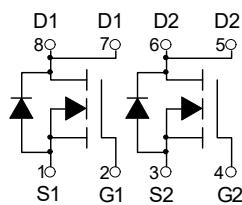
SOP-8

General Features

$V_{DS} = 40V$ $I_D = 12A$

$R_{DS(ON)} < 16m\Omega$ @ $V_{GS}=10 V$

$R_{DS(ON)} < 24m\Omega$ @ $V_{GS}=4.5V$



Application

Battery protection

Load switch

Uninterruptible power supply

Dual N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
NTMD5838NL	SOP-8	HXY MOSFET	3000

Absolute Maximum Ratings@ $T_j=25^\circ C$ (unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_A=25^\circ C$	Drain Current, $V_{GS} @ 4.5V^3$	12	A
$I_D @ T_A=70^\circ C$	Drain Current, $V_{GS} @ 4.5V^3$	7	A
I_{DM}	Pulsed Drain Current ¹	40	A
$P_D @ T_A=25^\circ C$	Total Power Dissipation	2.9	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C
R_{thj-a}	Maximum Thermal Resistance, Junction-ambient ³	65	°C/W

**Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	40	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}}=40\text{V}, V_{\text{GS}}=0\text{V}$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{\text{GS}}=\pm 20\text{V}, V_{\text{DS}}=0\text{V}$	-	-	± 100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	1	1.5	2.0	V
Drain-Source On-State Resistance	$R_{\text{DS(ON)}}$	$V_{\text{GS}}=10\text{V}, I_{\text{D}}=8\text{A}$	-	12.0	16	$\text{m}\Omega$
		$V_{\text{GS}}=4.5\text{V}, I_{\text{D}}=4\text{A}$	-	18.9	24	$\text{m}\Omega$
Forward Transconductance	g_{FS}	$V_{\text{DS}}=5\text{V}, I_{\text{D}}=8\text{A}$	33	-	-	S
Dynamic Characteristics (Note 4)						
Input Capacitance	C_{iss}	$V_{\text{DS}}=20\text{V}, V_{\text{GS}}=0\text{V}, F=1.0\text{MHz}$	-	964	-	PF
Output Capacitance	C_{oss}		-	109	-	PF
Reverse Transfer Capacitance	C_{rss}		-	96	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{\text{d(on)}}$	$V_{\text{DD}}=20\text{V}, R_{\text{L}}=2.5\Omega, V_{\text{GS}}=10\text{V}, R_{\text{GEN}}=3\Omega$	-	5.5	-	nS
Turn-on Rise Time	t_r		-	14	-	nS
Turn-Off Delay Time	$t_{\text{d(off)}}$		-	24	-	nS
Turn-Off Fall Time	t_f		-	12	-	nS
Total Gate Charge	Q_g	$V_{\text{DS}}=20\text{V}, I_{\text{D}}=8\text{A}, V_{\text{GS}}=10\text{V}$	-	22.9	-	nC
Gate-Source Charge	Q_{gs}		-	3.5	-	nC
Gate-Drain Charge	Q_{gd}		-	5.3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{\text{GS}}=0\text{V}, I_{\text{S}}=9\text{A}$	-	0.8	1.2	V



Typical Electrical and Thermal Characteristics (Curves)

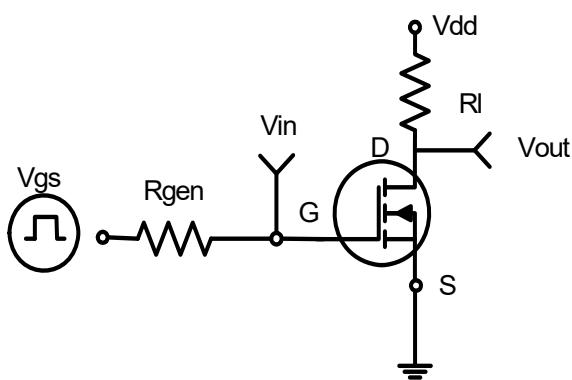


Figure 1:Switching Test Circuit

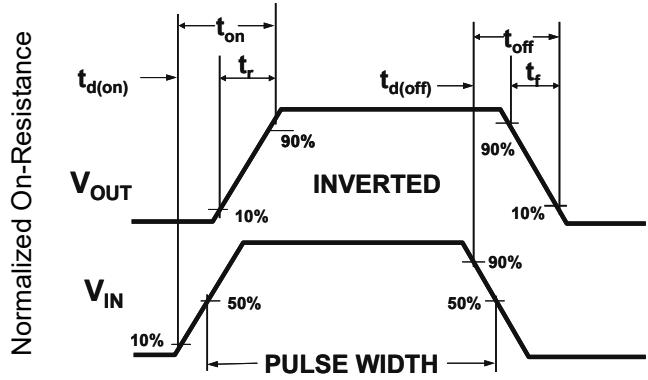


Figure 2:Switching Waveforms

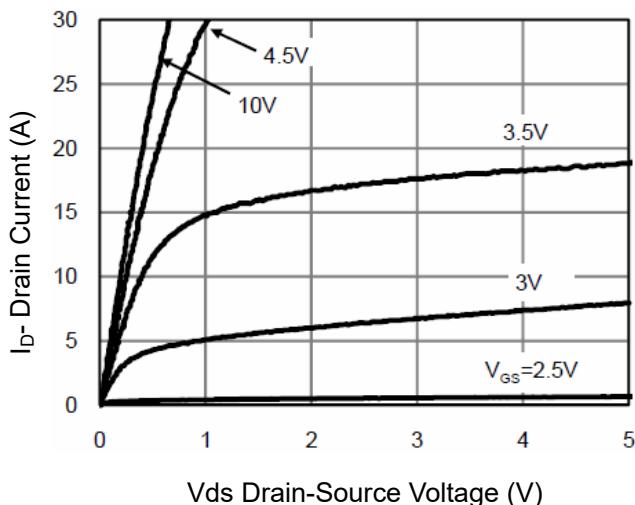


Figure 3 Output Characteristics

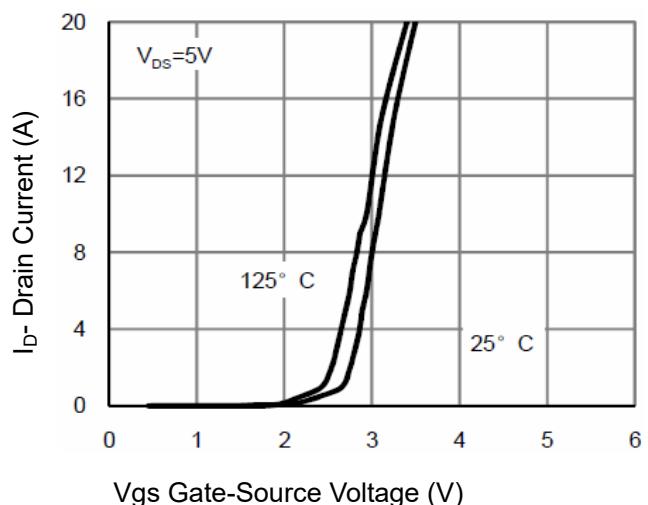


Figure 4 Transfer Characteristics

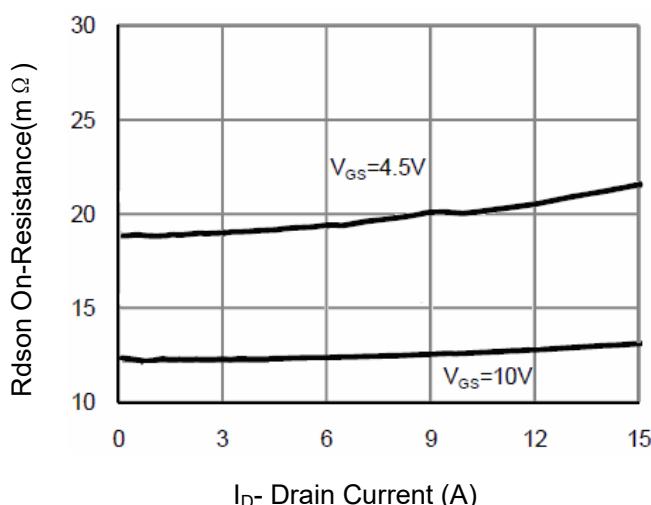


Figure 5 Drain-Source On-Resistance

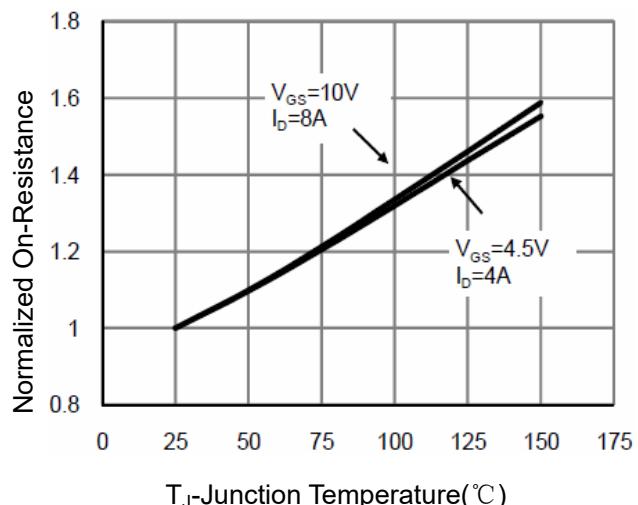
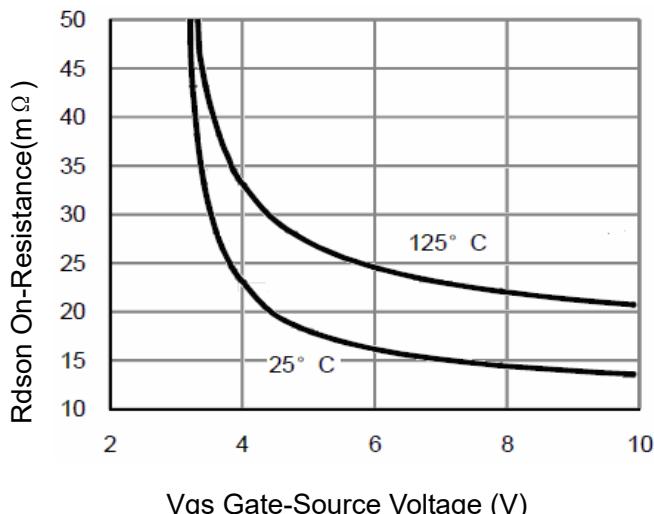
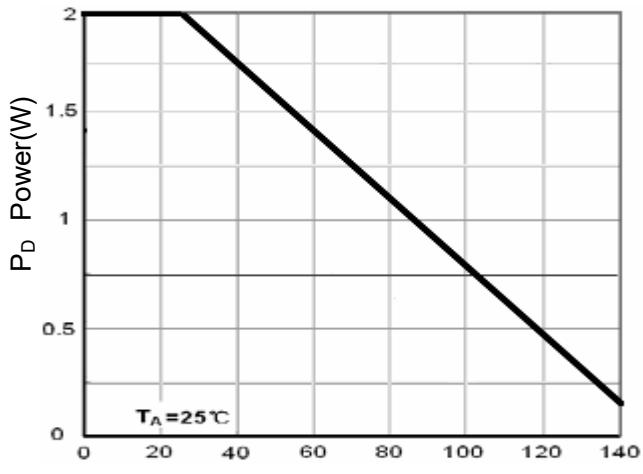


Figure 6 Drain-Source On-Resistance



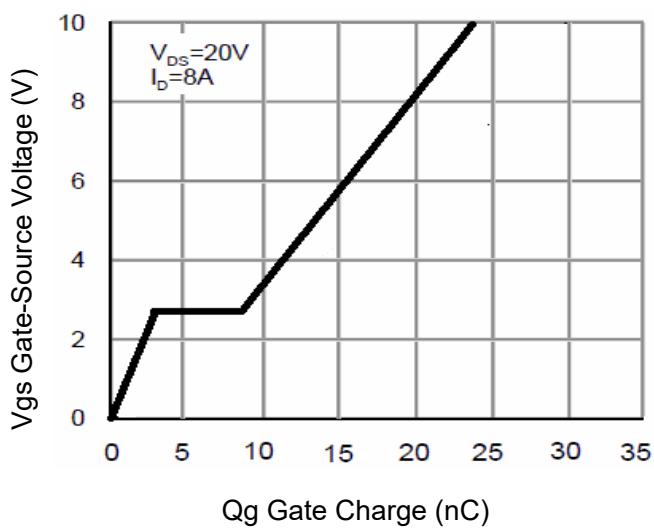
V_{GS} Gate-Source Voltage (V)

Figure 7 $R_{DS(on)}$ vs V_{GS}



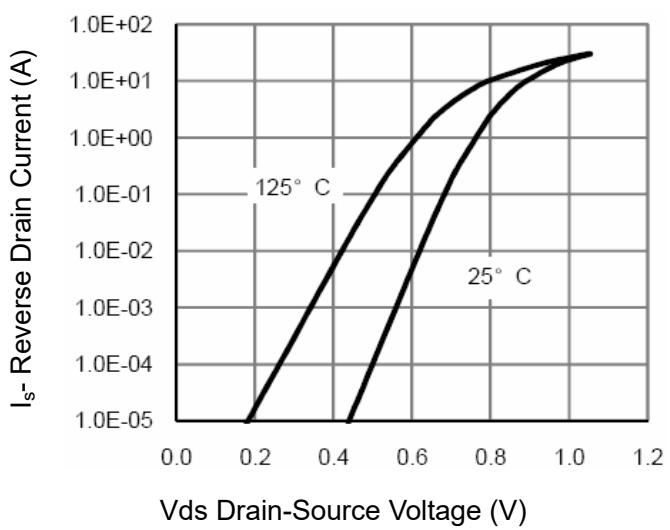
T_J -Junction Temperature (°C)

Figure 8 Power Dissipation



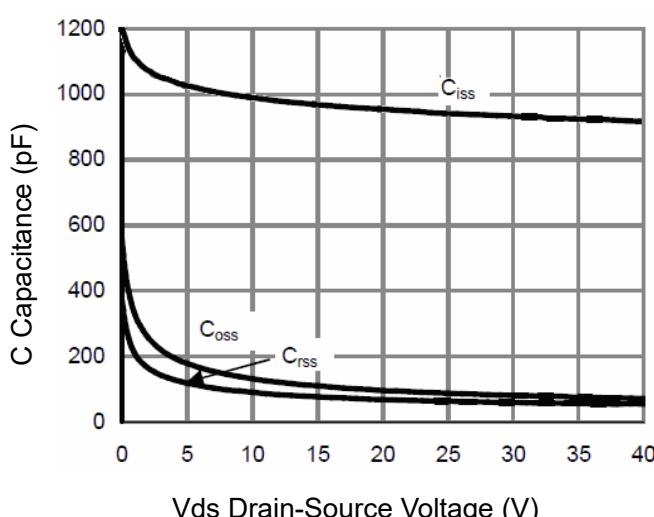
Q_g Gate Charge (nC)

Figure 9 Gate Charge



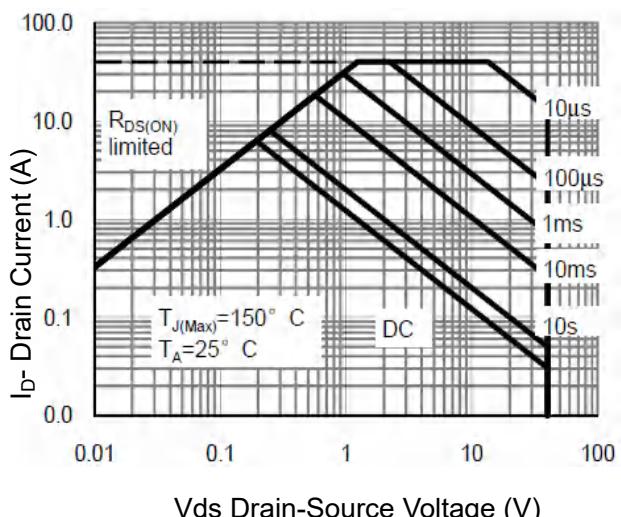
V_{DS} Drain-Source Voltage (V)

Figure 10 Source- Drain Diode Forward



V_{DS} Drain-Source Voltage (V)

Figure 11 Capacitance vs V_{DS}

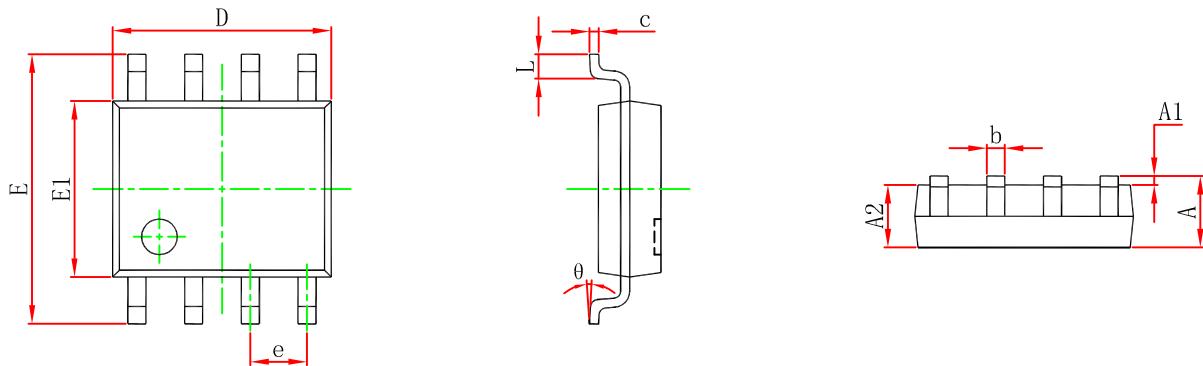


V_{DS} Drain-Source Voltage (V)

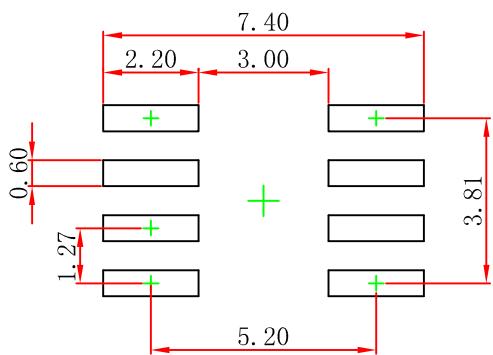
Figure 12 Safe Operation Area



SOP-8 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.800	5.000	0.189	0.197
e	1.270 (BSC)		0.050 (BSC)	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
θ	0°		8°	



Note:
1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.05 mm.
3. The pad layout is for reference purposes only.



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